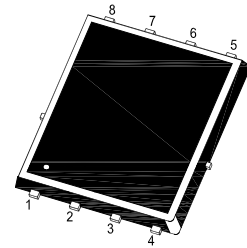
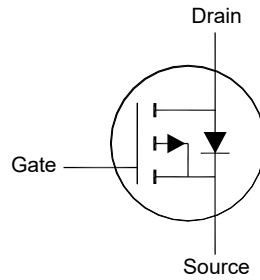


WTM504P400LS-CH

P-Channel Enhancement Mode MOSFET

Features

- AEC-Q101 Qualified
- Surface-mounted package
- Halogen and Antimony Free(HAF), RoHS compliant



1.Source 2.Source 3.Source 4.Gate
5.Drain 6.Drain 7.Drain 8.Drain
DFN5060 Plastic Package

Key Parameters

Parameter	Value	Unit
$-BV_{DSS}$	40	V
$R_{DS(ON)}$ Max	40 @ $-V_{GS} = 10$ V	m Ω
	55 @ $-V_{GS} = 4.5$ V	
$-V_{GS(th)}$ typ	1.5	V
Q_g typ	19 @ $-V_{GS} = 10$ V	nC

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$-V_{DS}$	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	$-I_D$	$T_c = 25^\circ\text{C}$	23
		$T_c = 100^\circ\text{C}$	14.5
Peak Drain Current, Pulsed ¹⁾	$-I_{DM}$	60	A
Single-Pulse Avalanche Current	$-I_{AS}$	16.8	A
Single-Pulse Avalanche Energy ²⁾	E_{AS}	14.1	mJ
Power Dissipation	P_D	34.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$

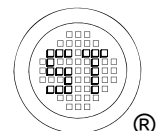
Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.6	$^\circ\text{C/W}$
Thermal Resistance from Junction to Ambient ³⁾	$R_{\theta JA}$	45	$^\circ\text{C/W}$

¹⁾ Pulse Test: Pulse Width ≤ 100 μs , Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.

²⁾ Limited by $T_{J(MAX)}$, starting $T_J = 25^\circ\text{C}$, $L = 0.1$ mH, $R_g = 25$ Ω , $-I_{AS} = 16.8$ A, $-V_{GS} = 10$ V.

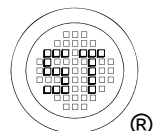
³⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.



WTM504P400LS-CH

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $-I_D = 250 \mu\text{A}$	$-BV_{DSS}$	40	-	-	V
Drain-Source Leakage Current at $-V_{DS} = 40 \text{ V}$	$-I_{DSS}$	-	-	1	μA
Gate Leakage Current at $V_{GS} = \pm 20 \text{ V}$	I_{GSS}	-	-	± 100	nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}, -I_D = 250 \mu\text{A}$	$-V_{GS(th)}$	1.0	-	2.5	V
Drain-Source On-State Resistance at $-V_{GS} = 10 \text{ V}, -I_D = 12 \text{ A}$ at $-V_{GS} = 4.5 \text{ V}, -I_D = 10 \text{ A}$	$R_{DS(on)}$	- -	31 -	40 55	m Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $-V_{DS} = 5 \text{ V}, -I_D = 10 \text{ A}$	g_{FS}	-	18.7	-	S
Gate Resistance at $V_{GS} = 0 \text{ V}, V_{DS} = 0 \text{ V}, f = 1 \text{ MHz}$	R_g	-	6	-	Ω
Input Capacitance at $-V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{iss}	-	1078	-	pF
Output Capacitance at $-V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{oss}	-	80	-	pF
Reverse Transfer Capacitance at $-V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	C_{rss}	-	42	-	pF
Total Gate Charge at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}$ at $-V_{GS} = 4.5 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}$	Q_g	- -	19 8	- -	nC
Gate-Source Charge at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}$	Q_{gs}	-	4	-	nC
Gate-Drain Charge at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}$	Q_{gd}	-	3	-	nC
Turn-On Delay Time at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}, R_G = 3.3 \Omega$	$t_{d(on)}$	-	8	-	ns
Turn-On Rise Time at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}, R_G = 3.3 \Omega$	t_r	-	27	-	ns
Turn-Off Delay Time at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}, R_G = 3.3 \Omega$	$t_{d(off)}$	-	14	-	ns
Turn-Off Fall Time at $-V_{GS} = 10 \text{ V}, -V_{DS} = 20 \text{ V}, -I_D = 12 \text{ A}, R_G = 3.3 \Omega$	t_f	-	3	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $-I_S = 1 \text{ A}, V_{GS} = 0 \text{ V}$	$-V_{SD}$	-	-	1.2	V
Body-Diode Continuous Current	$-I_S$	-	-	23	A
Body-Diode Continuous Current, Pulsed	$-I_{SM}$	-	-	60	A
Body Diode Reverse Recovery Time at $-I_S = 12 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	t_{rr}	-	10	-	ns
Body Diode Reverse Recovery Charge at $-I_S = 12 \text{ A}, di/dt = 100 \text{ A} / \mu\text{s}$	Q_{rr}	-	5	-	nC



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

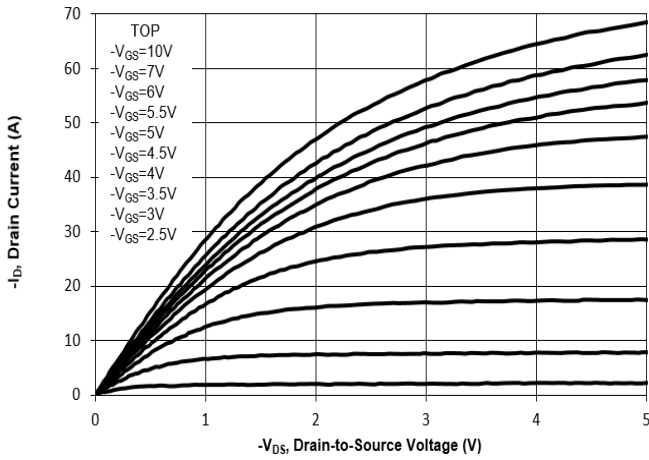


Fig. 2 Typical Transfer Characteristics

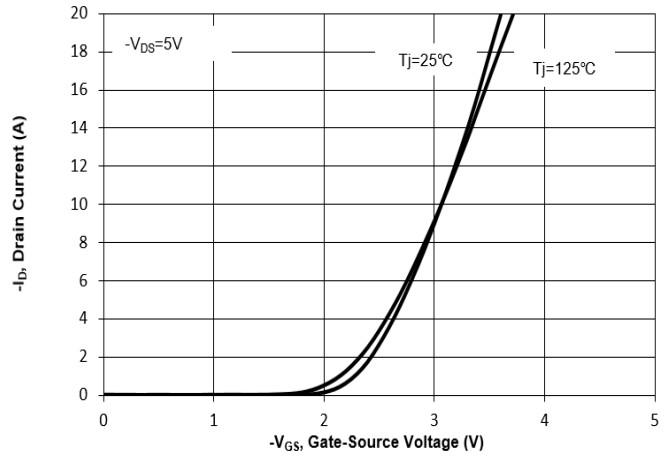


Fig. 3 On-Resistance vs. Drain Current

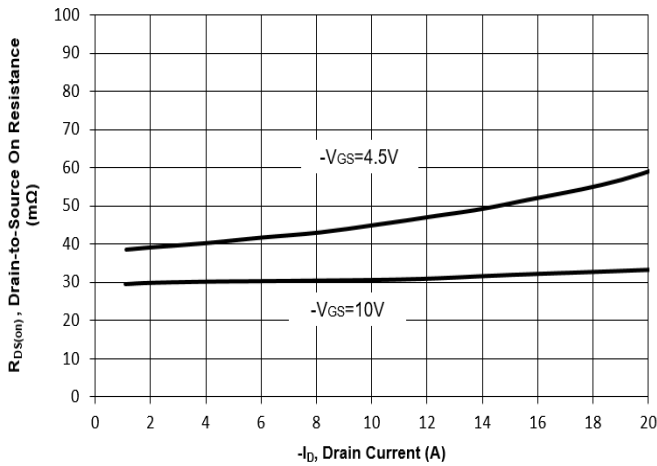


Fig. 4 On-Resistance vs. Gate to Source Voltage

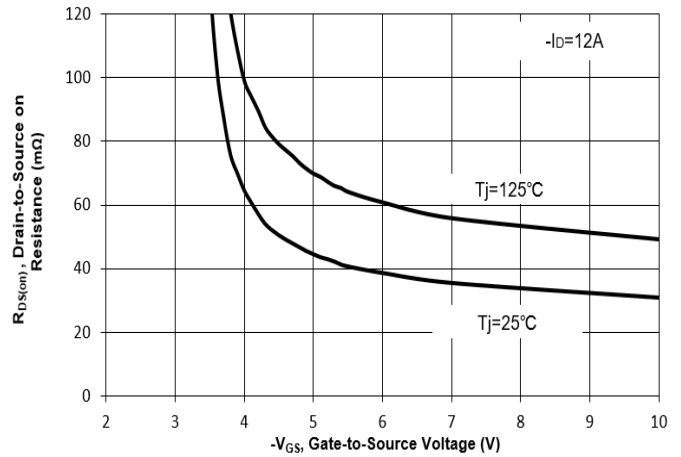


Fig. 5 On-Resistance vs. T_J

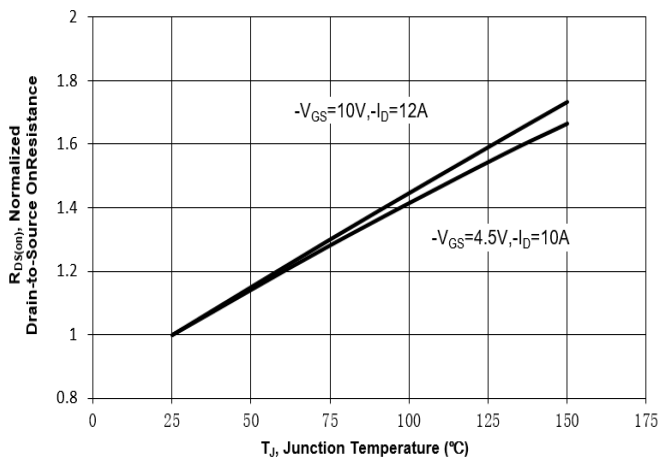
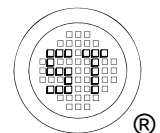
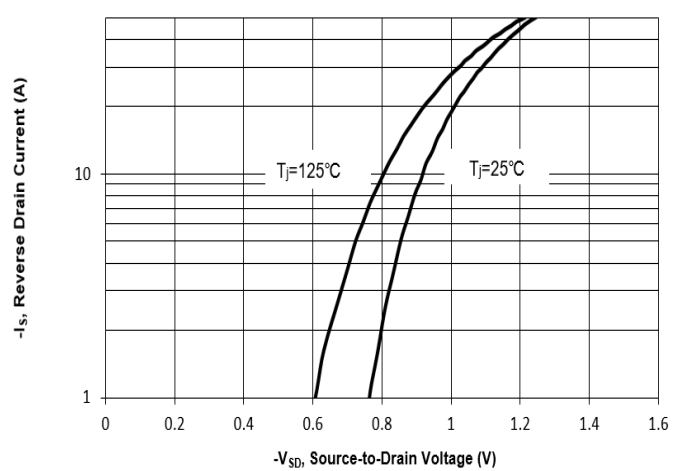


Fig. 6 Typical Body-Diode Forward Characteristics



WTM504P400LS-CH

Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

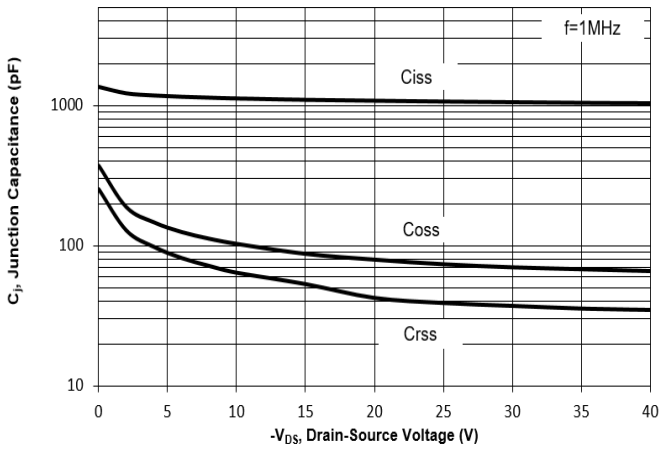


Fig. 8 Drain-Source Leakage Current vs. Tj

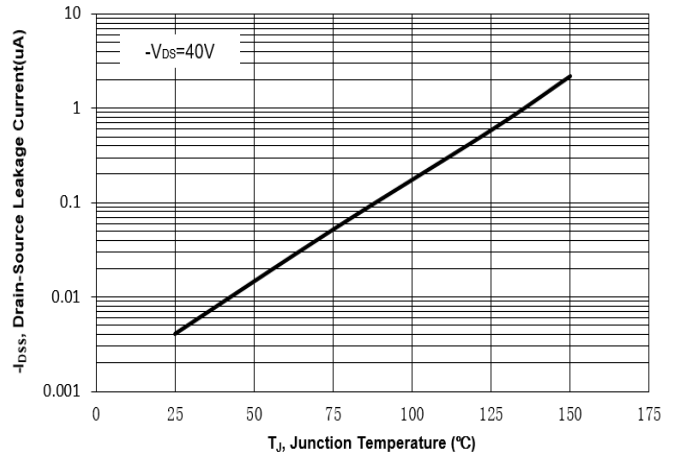


Fig. 9 V(BR)DSS vs. Junction Temperature

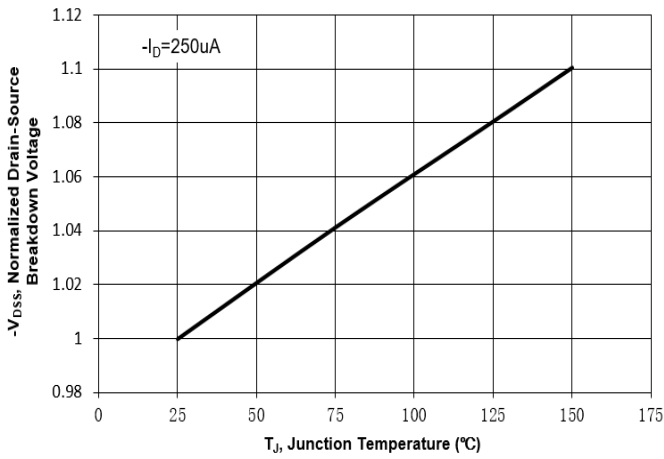


Fig. 10 Gate Threshold Variation vs. Tj

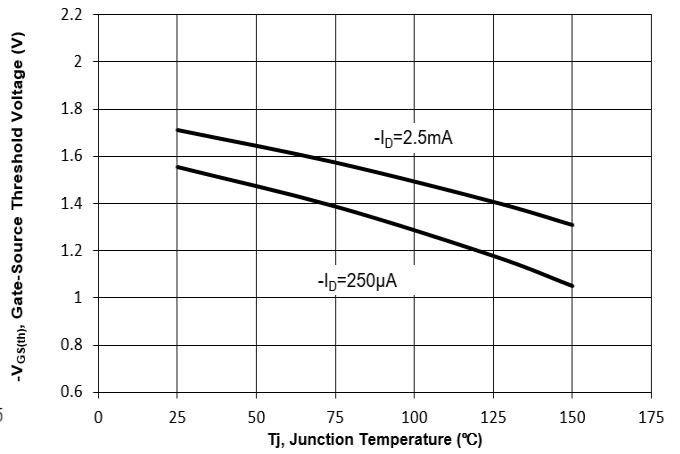


Fig. 11 Gate Charge

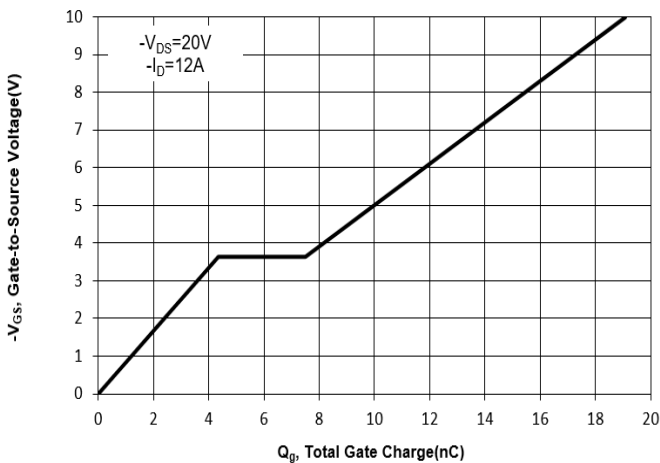
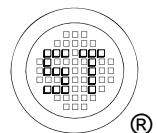
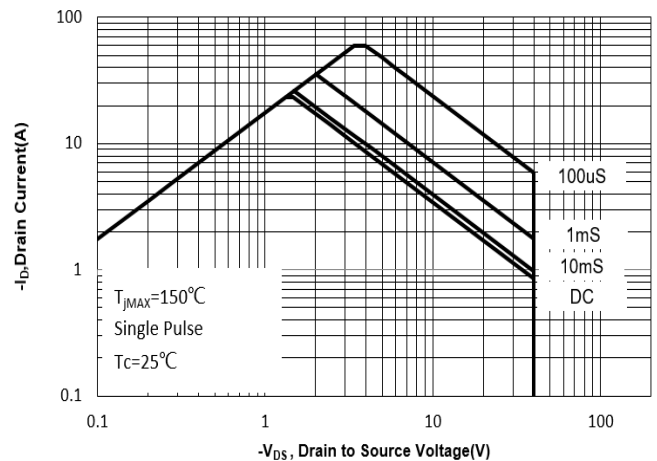


Fig. 12 Safe Operation Area



WTM504P400LS-CH

Electrical Characteristics Curves

Fig. 13 Normalized Maximum Transient Thermal Impedance($z_{\theta JC}$)

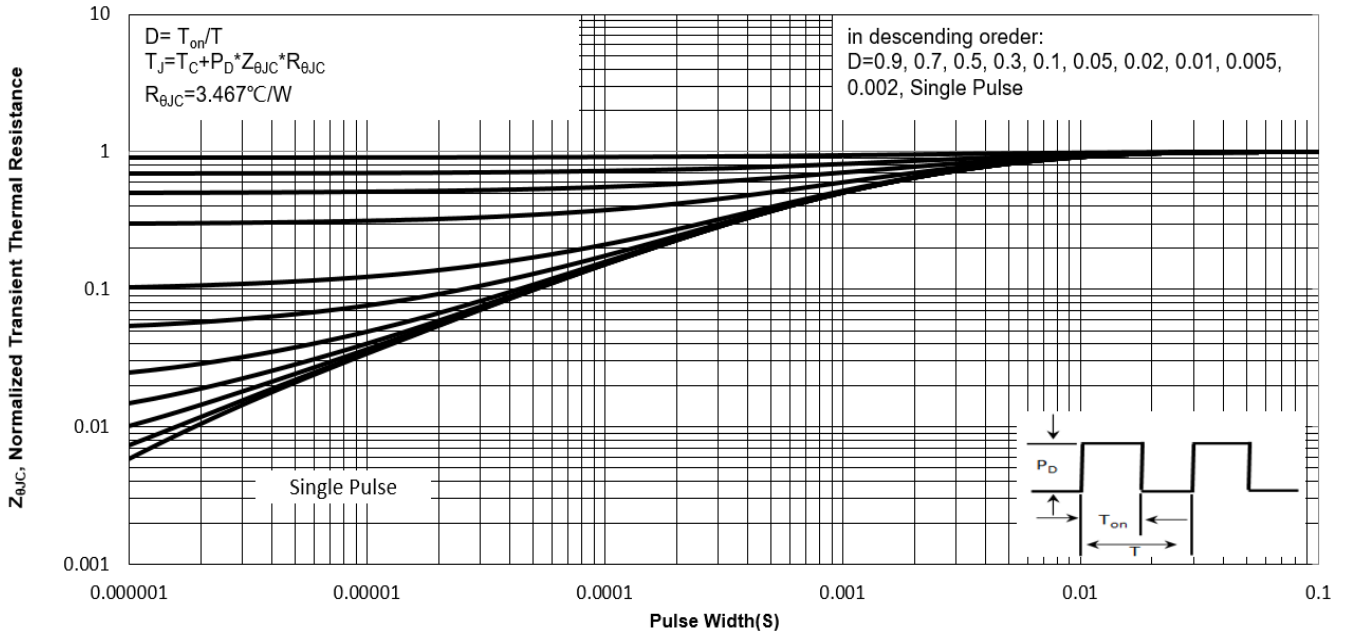
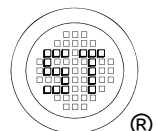
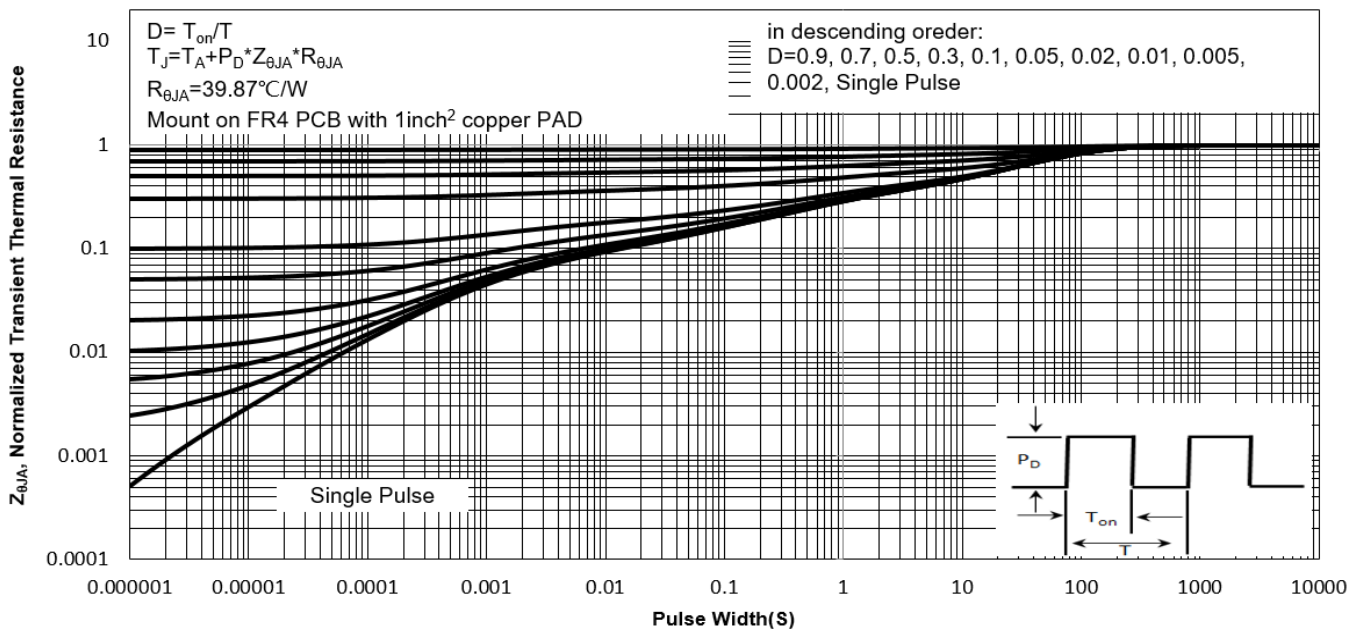


Fig. 14 Normalized Maximum Transient Thermal Impedance($z_{\theta JA}$)



Test Circuits

Fig.1-1 Switching times test circuit

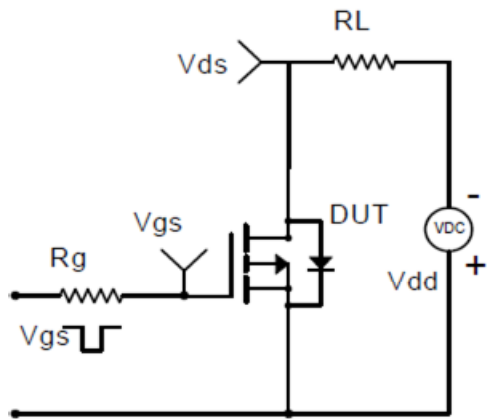


Fig.1-2 Switching Waveform

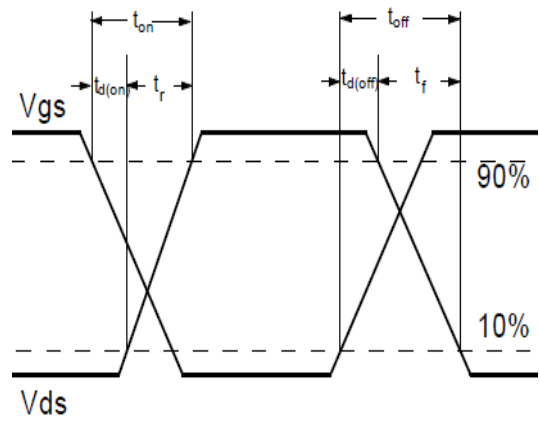


Fig.2-1 Gate charge test circuit

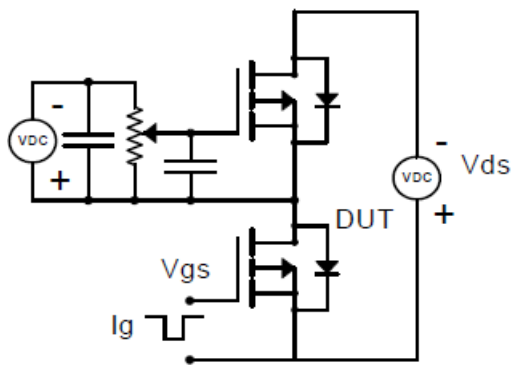


Fig.2-2 Gate charge waveform

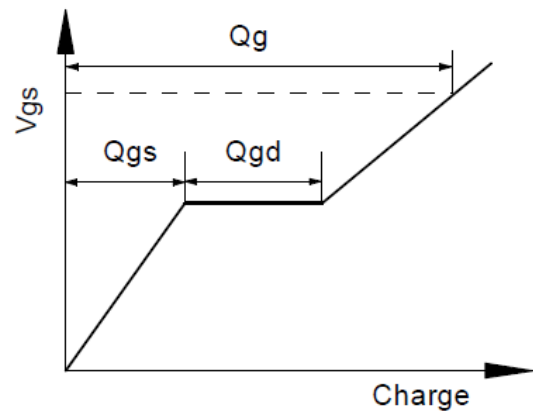


Fig.3-1 Avalanche test circuit

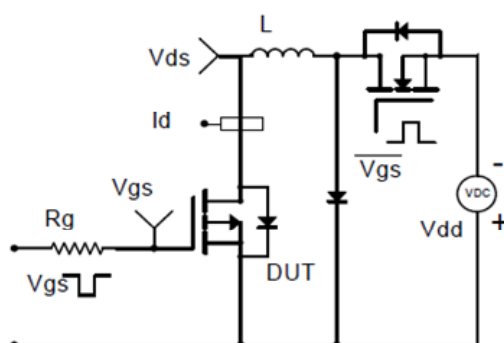
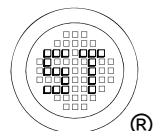
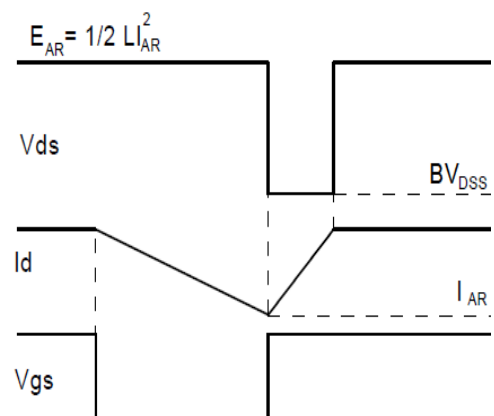


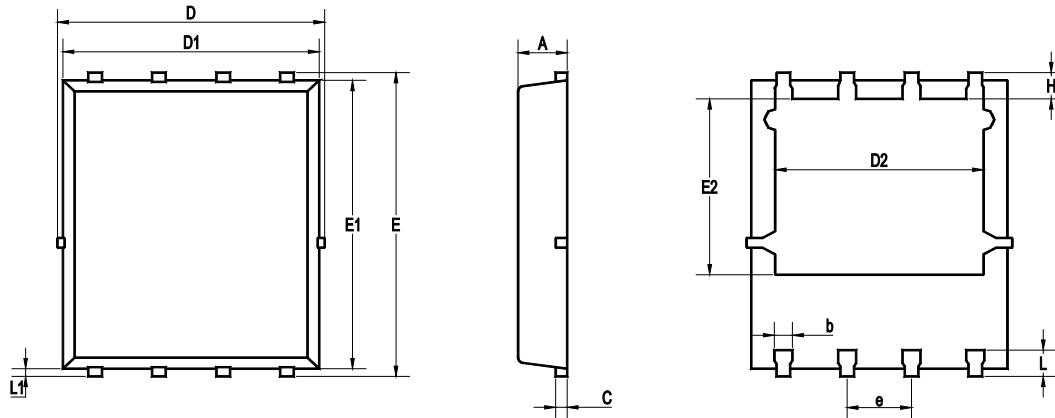
Fig.3-2 Avalanche waveform



WTM504P400LS-CH

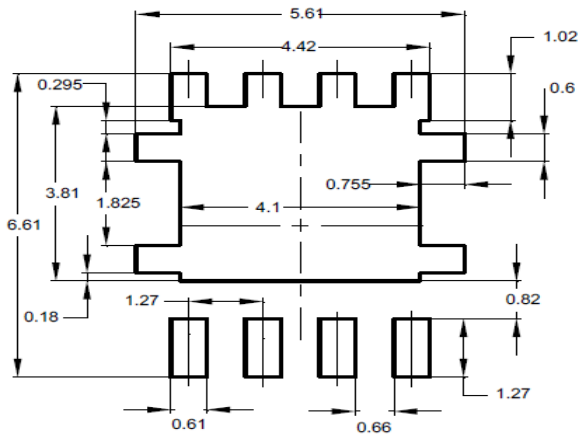
Package Outline Dimensions (Units: mm)

DFN5060



UNIT	A	b	C	D	D1	D2	E	E1	E2	e	L	L1	H
mm	1.12	0.51	0.34	5.26	5.1	4.5	6.25	6	3.66	1.37	0.71	0.2	0.71
	0.9	0.33	0.11	4.7	4.7	3.56	5.75	5.6	3.18	1.17	0.35	0.06	0.35

Recommended Soldering Footprint



Packing information

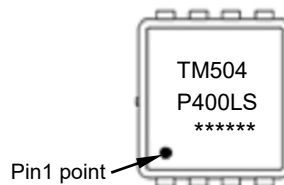
Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN5060	12	8 ± 0.1	0.315 ± 0.004	330	13	5,000

Marking information

" TM504P400LS " = Part No.

" ***** " = Date Code Marking

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice.

